
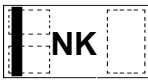
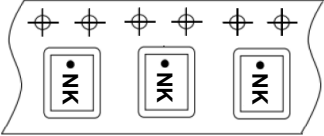
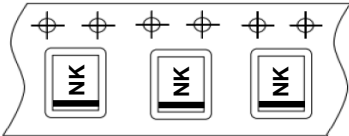

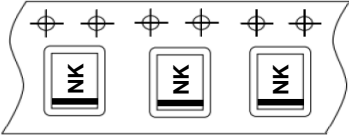


## Marking Information

|               |  |
|---------------|--|
| DMN62D0LFB-7  | <div style="display: flex; justify-content: space-around; align-items: flex-start;"> <div style="text-align: center;">  <p>Top View<br/>Dot Denotes Drain Side</p> </div> <div style="text-align: center;"> <p>From date code 1527 (YYWW),<br/>this changes to:</p>  <p>Top View<br/>Bar Denotes Gate and Source Side</p> </div> </div> <div style="display: flex; justify-content: space-around; align-items: center; margin-top: 10px;">   </div> |
| DMN62D0LFB-7B | <div style="text-align: center; margin-bottom: 10px;">  <p>Top View<br/>Bar Denotes Gate and Source Side</p> </div> <div style="display: flex; justify-content: space-between; align-items: center;">  <p>NK = Part Marking Code</p> </div>   |

## Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic  |                 |                        | Symbol           | Value | Unit |
|---|-----------------|------------------------|------------------|-------|------|
| Drain-Source Voltage  |                 |                        | V <sub>DSS</sub> | 60    | V    |
| Gate-Source Voltage   |                 |                        | V <sub>GSS</sub> | ±20   | V    |
| Continuous Drain Current (Note 5)<br>V <sub>GS</sub> = 4.0V | Steady<br>State | T <sub>A</sub> = +25°C | I <sub>D</sub>   | 320   | mA   |
|   |                 | T <sub>A</sub> = +70°C |                  | 75    |      |
| Pulsed Drain Current (Note 6)                               |                 |                        | I <sub>DM</sub>  | 1     | A    |

## Thermal Characteristics

| Characteristic   | Symbol                            | Max         | Unit |
|--|-----------------------------------|-------------|------|
| Power Dissipation (Note 5)   | P <sub>D</sub>                    | 0.5         | W    |
| Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C (Note 5) | R <sub>θJA</sub>                  | 258         | °C/W |
| Operating and Storage Temperature Range                                  | T <sub>J</sub> , T <sub>STG</sub> | -55 to +150 | °C   |

Notes: 5. Device mounted on FR-4 PCB with minimum recommended pad layout, single sided.  
 6. Repetitive rating, pulse width limited by junction temperature.

**Electrical Characteristics** (@  $T_A = +25^\circ\text{C}$ , unless otherwise stated.)

| Characteristic   | Symbol              | Min | Typ  | Max  | Unit | Test Condition  |
|--|---------------------|-----|------|------|------|---|
| OFF CHARACTERISTICS (Note 7)                           |                     |     |      |      |      |   |
| Drain-Source Breakdown Voltage                         | BV <sub>DSS</sub>   | 60  | —    | —    | V    | V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA  |
| Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C | I <sub>DSS</sub>    | —   | —    | 1.0  | μA   | V <sub>DS</sub> = 60V, V <sub>GS</sub> = 0V   |
| Gate-Source Leakage                                    | I <sub>GSS</sub>    | —   | —    | ±100 | nA   | V <sub>GS</sub> = ±5V, V <sub>DS</sub> = 0V   |
|  |                     | —   | —    | ±500 | nA   | V <sub>GS</sub> = ±10V, V <sub>DS</sub> = 0V  |
|  |                     | —   | —    | ±2.0 | μA   | V <sub>GS</sub> = ±15V, V <sub>DS</sub> = 0V  |
| ON CHARACTERISTICS (Note 7)                            |                     |     |      |      |      |   |
| Gate Threshold Voltage                                 | V <sub>GS(TH)</sub> | 0.6 | —    | 1.0  | V    | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA  |
| Static Drain-Source On-Resistance                      | R <sub>DS(ON)</sub> | —   | 1.3  | 2    | Ω    | V <sub>GS</sub> = 4V, I <sub>D</sub> = 100mA  |
|  |                     | —   | 1.5  | 2.5  |      | V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 50mA   |
|  |                     | —   | 1.9  | 3    |      | V <sub>GS</sub> = 1.8V, I <sub>D</sub> = 50mA   |
|  |                     | —   | 2.6  | —    |      | V <sub>GS</sub> = 1.5V, I <sub>D</sub> = 10mA   |
| Forward Transfer Admittance                            | Y <sub>fs</sub>     | —   | 0.8  | —    | S    | V <sub>DS</sub> = 10V, I <sub>D</sub> = 200mA   |
| Diode Forward Voltage                                  | V <sub>SD</sub>     | —   | 0.9  | 1.3  | V    | V <sub>GS</sub> = 0V, I <sub>S</sub> = 115mA  |
| DYNAMIC CHARACTERISTICS (Note 8)                       |                     |     |      |      |      |   |
| Input Capacitance                                      | C <sub>iss</sub>    | —   | 32   | 64   | pF   | V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V,<br>f = 1.0MHz  |
| Output Capacitance                                     | C <sub>oss</sub>    | —   | 4.4  | 9    |      |   |
| Reverse Transfer Capacitance                           | C <sub>rss</sub>    | —   | 2.9  | 6    |      |   |
| Gate Resistance  | R <sub>g</sub>      | —   | 126  | 250  | Ω    | V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz  |
| Total Gate Charge                                      | Q <sub>g</sub>      | —   | 0.45 | 0.9  | nC   | V <sub>GS</sub> = 4.5V, V <sub>DS</sub> = 10V,<br>I <sub>D</sub> = 250mA  |
| Gate-Source Charge                                     | Q <sub>gs</sub>     | —   | 0.08 | 0.2  |      |   |
| Gate-Drain Charge                                      | Q <sub>gd</sub>     | —   | 0.08 | 0.2  |      |   |
| Turn-On Delay Time                                     | t <sub>D(ON)</sub>  | —   | 3.4  | 10   | ns   | V <sub>GS</sub> = 10V, V <sub>DS</sub> = 30V,<br>R <sub>L</sub> = 150Ω, R <sub>g</sub> = 25Ω,<br>I <sub>D</sub> = 200mA |
| Turn-On Rise Time                                      | t <sub>r</sub>      | —   | 3.4  | 10   | ns   |   |
| Turn-Off Delay Time                                    | t <sub>D(OFF)</sub> | —   | 26.4 | 45   | ns   |   |
| Turn-Off Fall Time                                     | t <sub>f</sub>      | —   | 16.3 | 30   | ns   |   |

Notes: 7. Short duration pulse test used to minimize self-heating effect.  
8. Guaranteed by design. Not subject to production testing.

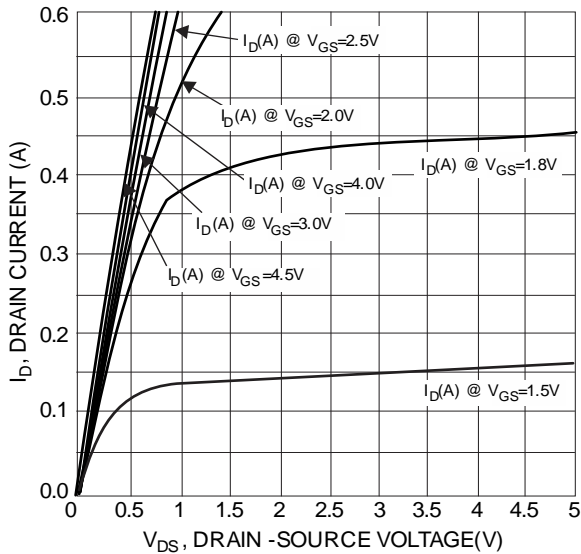


Fig. 1 Typical Output Characteristics

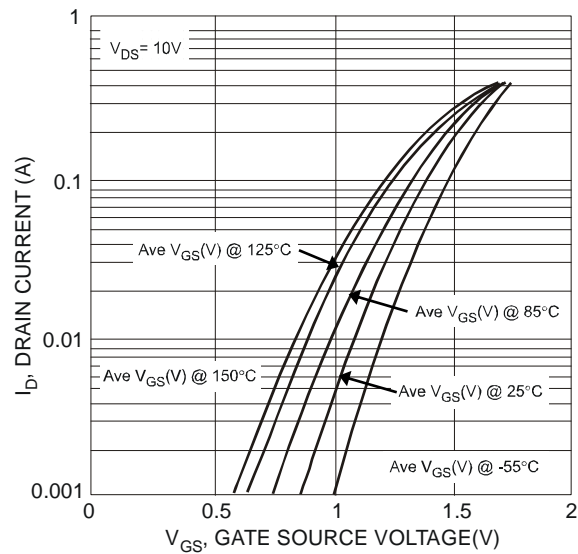
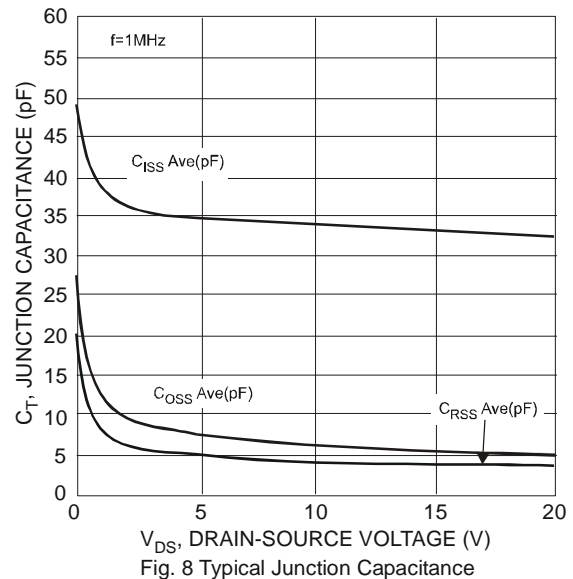
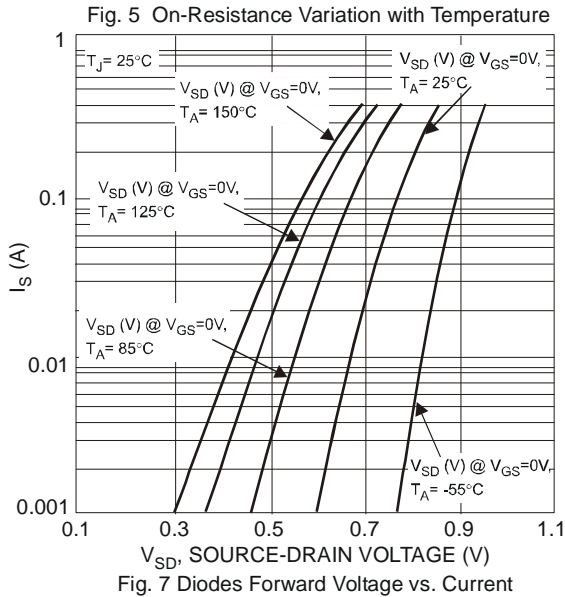
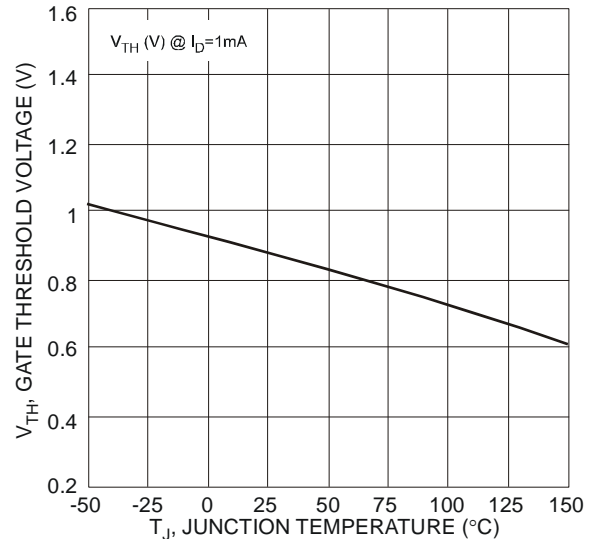
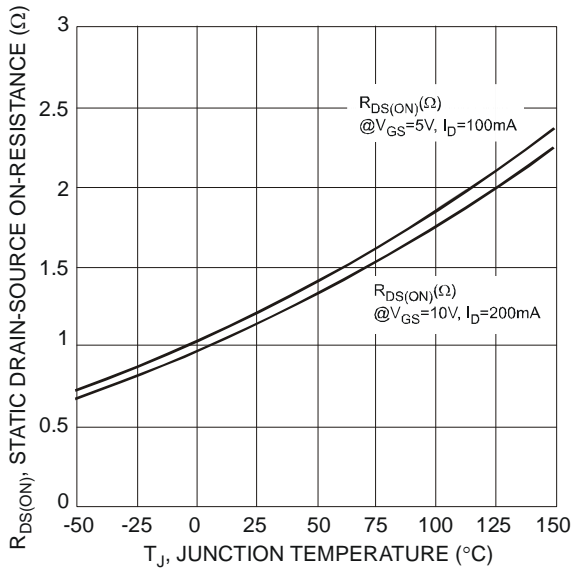
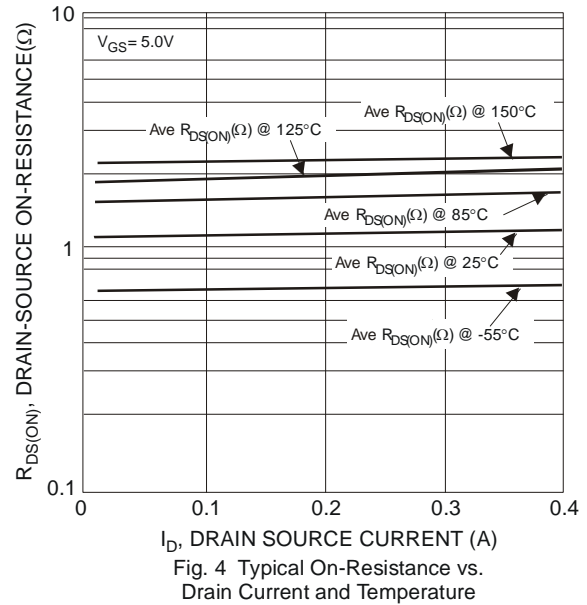
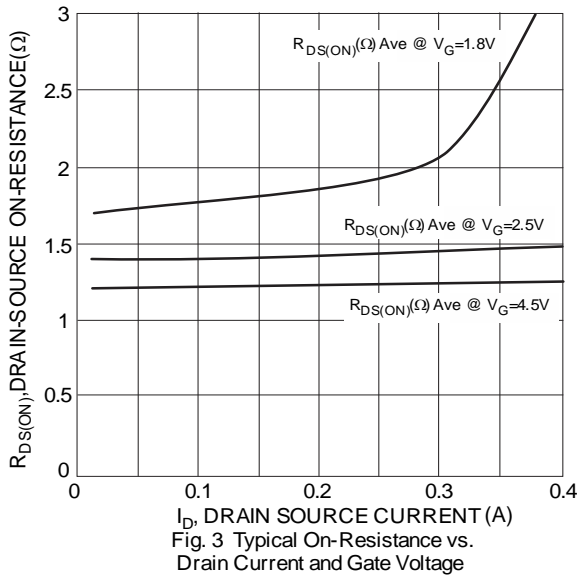
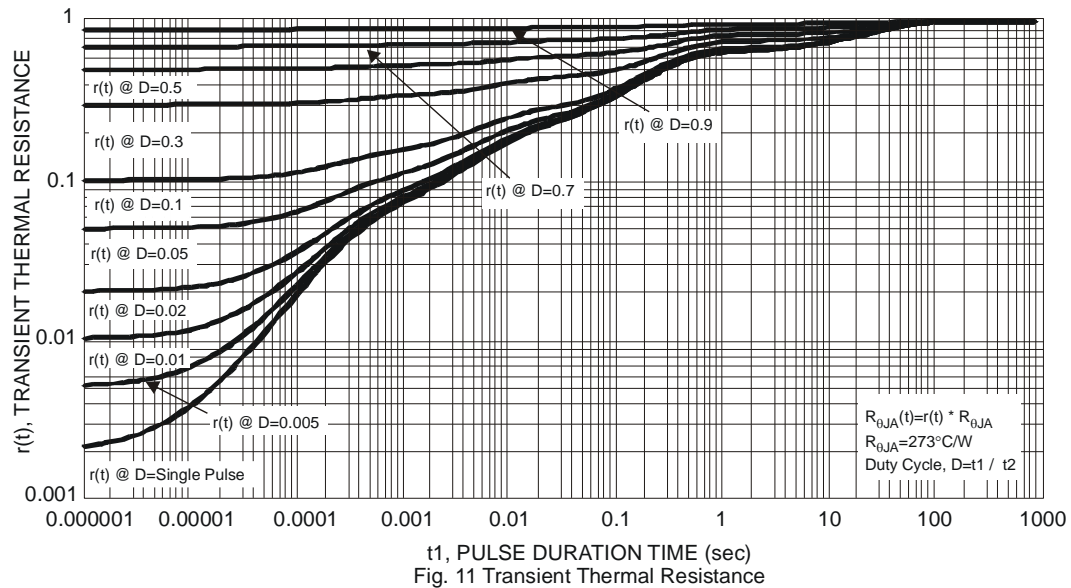
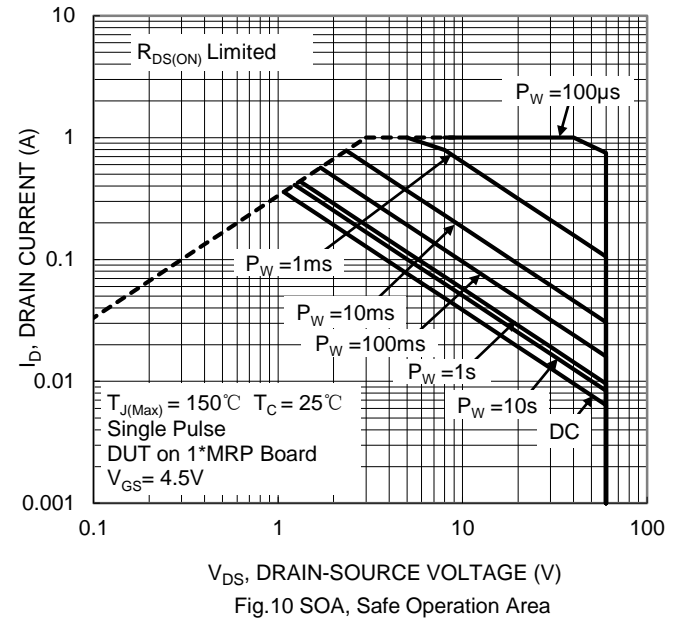
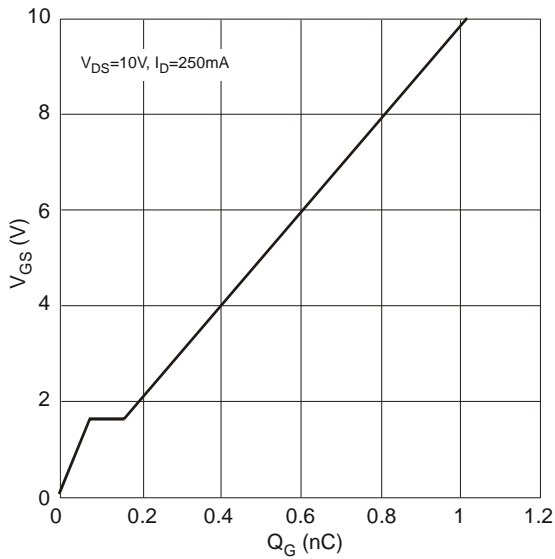


Fig. 2 Typical Transfer Characteristics

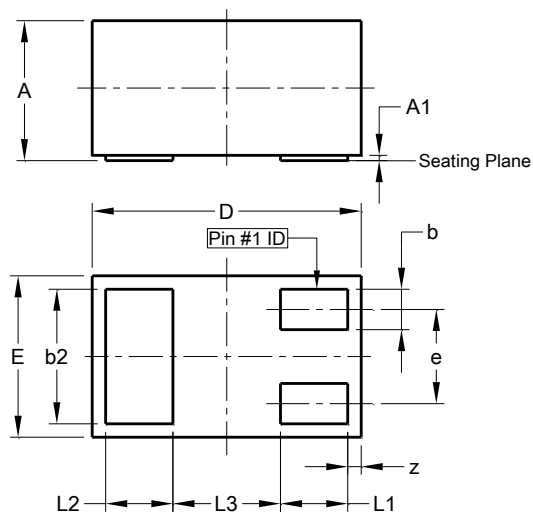




## Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

X1-DFN1006-3

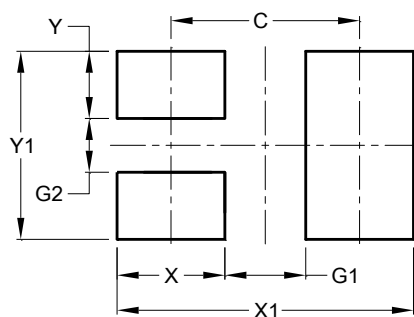


| X1-DFN1006-3         |      |       |      |
|----------------------|------|-------|------|
| Dim                  | Min  | Max   | Typ  |
| A                    | 0.47 | 0.53  | 0.50 |
| A1                   | 0.00 | 0.05  | 0.03 |
| b                    | 0.10 | 0.20  | 0.15 |
| b2                   | 0.45 | 0.55  | 0.50 |
| D                    | 0.95 | 1.075 | 1.00 |
| E                    | 0.55 | 0.675 | 0.60 |
| e                    | -    | -     | 0.35 |
| L1                   | 0.20 | 0.30  | 0.25 |
| L2                   | 0.20 | 0.30  | 0.25 |
| L3                   | -    | -     | 0.40 |
| z                    | 0.02 | 0.08  | 0.05 |
| All Dimensions in mm |      |       |      |

## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

X1-DFN1006-3



| Dimensions | Value (in mm) |
|------------|---------------|
| C          | 0.70          |
| G1         | 0.30          |
| G2         | 0.20          |
| X          | 0.40          |
| X1         | 1.10          |
| Y          | 0.25          |
| Y1         | 0.70          |

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